

CMOS Ionization Smoke Detector ASIC with Interconnect, Timer Mode and Alarm Memory

Features

- Pin Selectable Horn Patterns
- Alarm Memory
- Sensitivity Control Timer:
 - 8 minute Timer for RE46C162
 - 1 minute Timer for RE46C163
- >1500V ESD Protection (HBM) on All Pins
- · Guard Outputs for Ion Detector Input
- ±0.75 pA Detect Input Current
- Internal Reverse Battery Protection
- Low Quiescent Current Consumption (<6.5 μA)
- I/O Filter and Charge Dump
- Internal Low Battery Detection
- · Power-up Low Battery Test
- · Interconnect up to 66 Detectors
- RoHS Compliant, Lead Free Packaging

Description

The RE46C162/163 devices are low-power, CMOS ionization type, smoke detector ICs. With few external components, these circuits will provide all the required features for an ionization type smoke detector.

An internal oscillator strobes power to the smoke detection circuitry for 10.5 ms every 1.67 seconds to keep standby current to a minimum. A check for a low battery condition is performed every 40 seconds when in standby. The temporal horn pattern supports the NFPA 72 emergency evacuation signal.

An interconnect pin allows multiple detectors to be connected so when one unit alarms, all units will sound. A charge dump feature will quickly discharge the interconnect line when exiting a local alarm. The interconnect input is also digitally filtered.

An internal timer allows for a single button, push-to-test to be used for a reduced sensitivity mode.

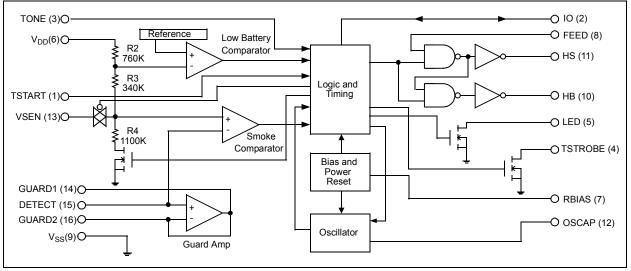
An alarm memory feature allows the user to determine if the unit has previously entered a local alarm condition.

Utilizing low-power CMOS technology, the RE46C162/163 devices are designed for use in smoke detectors that comply with Underwriters Laboratory Specification UL217 and UL268.

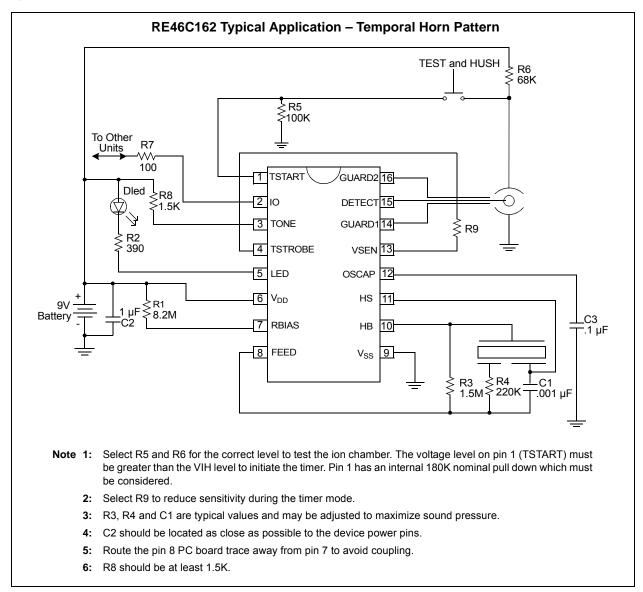
Package Types

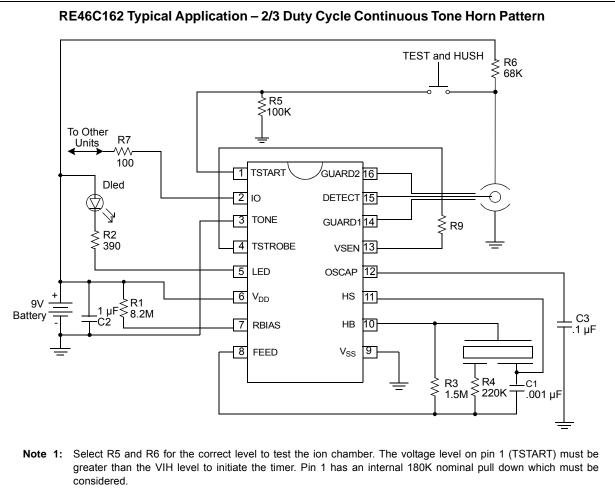
RE46C162/163 PDIP								
TSTART	1 16	GUARD2						
IO 🗌	2 15	DETECT						
TONE	3 14	GUARD1						
TSTROBE	4 13	VSEN						
LED	5 12	OSCAP						
V _{DD}	6 11	HS						
RBIAS	7 10	НВ						
FEED	8 9	□ v _{ss}						

Functional Block Diagram



Typical Applications





- 2: Select R9 to reduce sensitivity during the timer mode.
- 3: R3, R4 and C1 are typical values and may be adjusted to maximize sound pressure.
- 4: C2 should be located as close as possible to the device power pins.
- 5: Route the pin 8 PC board trace away from pin 7 to avoid coupling.

1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings†

V _{DD} 15V
Input Voltage Range Except FEED, I/O $\rm V_{IN}\mbox{=}3V$ to $\rm V_{DD}\mbox{+.}3V$
FEED Input Voltage Range V_{INFD} = -10 to +22V
I/O Input Voltage RangeV _{IO1} =3 to 15V
Reverse Battery Time T_{RB} = 5S
Input Current except FEEDI _{IN} = 10 mA
Operating Temperature $T_A = -10$ to $+60^{\circ}C$
Storage TemperatureT _{STG} = -55 to +125°C
Maximum Junction Temperature

† Notice: Stresses above those listed under "Maximum ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Test	Min	Тур	Max	Units	Conditions
		Pin		71			
Supply Voltage	V _{DD}	6	6	—	12	V	Operating
Supply Current	I _{DD1}	6		5	6.5	μA	RBIAS = 8.2 MW, OSCAP = $.1 \mu F$
	I _{DD2}	6	—	—	9	μA	RBIAS = 8.2 MW, OSCAP = .1 μ F; V _{DD} = 12V
Input Voltage High	V _{IH1}	3,8	6.2	4.5	_	V	Note 2
	V _{IH2}	2	3			V	No local alarm, I/O as an input
	V _{IH3}	1	4.5	—	_	V	
Input Voltage Low	V _{IL1}	3,8	_	4.5	2.7	V	Note 2
	V _{IL2}	2	_	_	1	V	No local alarm, I/O as an input
	V _{IL3}	1	_	_	2.5	V	
Input Leakage Low	IL _{DET1}	15	_	_	-0.75	pА	V _{DD} = 9V, DETECT = V _{SS} , 0-40% RH
	IL _{DET2}	15		-	-1.50	pА	V _{DD} = 9V, DETECT = V _{SS} , 85% RH Note 1
	IL _{FD}	8		_	-50	μA	FEED = -10V
	IL _{TONE}	3		_	-100	nA	TONE = V _{SS}
Input Leakage High	IH _{DET1}	15		_	0.75	pА	V _{DD} = 9V, DETECT = V _{DD} , 0-40% RH
	IH _{DET2}	15	_	_	1.50	pА	V _{DD} = 9V, DETECT = V _{DD} , 85% RH Note 1
	IH _{FD}	8	_	_	50	μA	FEED = 22V
	I _{IOL2}	2	_	_	150	μA	No alarm, V _{IO} = 15V
	IH _{TONE}	3	—	—	100	nA	TONE = V _{DD}
Output Off Leakage High	I _{IOHZ}	4,5	_	_	1	μA	Outputs off
Input Pull Down Current	I _{PD1}	1	20	50	80	μA	TSTART = 9V
Output High Voltage	V _{OH1}	10,11	6.3	_		V	I _{OH} = -16 mA, V _{DD} = 7.2V

Note 1: Sample test only.

2: Not 100% production tested.

3: Production test at room with temperature guard banded limits.

DC ELECTRICAL CHARACTERISTICS (CONTINUED)

DC Electrical Characteristics: Unless otherwise indicated, all parameters apply at $T_A = +25^{\circ}C$, $V_{DD} = 9V$, OSCAP = .1 µF. RBIAS = 8.2 MΩ, $V_{SS} = 0V$

OSCAP = .1 μ F, RBIAS = 8.2 M Ω , V _{SS} = 0V								
Parameter	Symbol	Test Pin	Min	Тур	Max	Units	Conditions	
Output Low Voltage	V _{OL1}	10,11	-	_	.9	V	I _{OL} = 16 mA, V _{DD} = 7.2V	
	V _{OL2}	4			.5	V	I _{OL} = 500 μA	
	V _{OL3}	5	—	—	1	V	I _{OL} = 10 mA, V _{DD} = 7.2V	
Output Current	I _{IOL1}	2	25		60	μA	No alarm, V_{IO} = V_{DD} -2V	
	I _{IOH1}	2	-4	_	-16	mA	Alarm, $V_{IO} = V_{DD} - 2V$ or $V_{IO} = 0V$	
	I _{IODMP}	2	5	_	—	mA	At conclusion of local alarm or test, V_{IO} = 1V	
Low Battery Voltage	V _{LB}	6	7.2	7.5	7.8	V	T _A = -10 to +60°C, Note 3	
Internal Sensitivity Set Voltage	V _{SET1}	13	48.5	50	51.5	%V _{DD}		
Offset Voltage	VG _{OS1}	14,15	-50	_	50	mV	Guard amplifier	
	VG _{OS2}	15,16	-50	—	50	mV	Guard amplifier	
	VG _{OS3}	13,15	-50	_	50	mV	Smoke comparator	
Common Mode Voltage	V _{CM1}	14,15	2		V _{DD} - .5	V	Guard amplifier, Note 2	
	V _{CM2}	13,15	.5	_	V _{DD} -2	V	Smoke comparator, Note 2	
Output Impedance	Z _{OUT}	14,16	_	10	—	kW	Guard amplifier outputs, Note 2	
Hysteresis	V _{HYS}	13	90	130	170	mV	No alarm to alarm condition	

Note 1: Sample test only.

2: Not 100% production tested.

3: Production test at room with temperature guard banded limits.

AC ELECTRICAL CHARACTERISTICS

AC Electrical Characteristics: Unless otherwise indicated, all parameters apply at $T_A = +25^{\circ}C$, $V_{DD} = 9V$, OSCAP = .1 µF, RBIAS = 8.2 MΩ, $V_{SS} = 0V$.

Parameter	Symbol	Test Pin	Min	Тур	Мах	Units	Conditions		
Oscillator Period	T _{PER1}	12	1.34	1.67	2	s	No alarm condition		
	T _{PER2}	12	37.5	41.7	45.8	ms	Alarm condition		
Oscillator Pulse Width	T _{PW}	5	9.4	10.5	12.9	ms	Operating		
LED On Time	T _{LON}	5	9.4	10.5	12.9	ms	Operating		
LED Off Time	T _{LOF1}	5	32	40	48	s	Standby, no alarm		
	T _{LOF2}	5	.9	1	1.1	s	Alarm condition		
	T _{LOF3}	5	8	10	12	s	Timer mode, no alarm		
	T _{LOF4}	5	2.66	3.33	4	S	Alarm memory LED pulse spacing		
	T _{LOF5}	5	26	33.3	40	S	Alarm memory LED off time between pulse train		

Note 1: See timing diagram for horn temporal and non-temporal patterns.

2: T_{PER1}, T_{PER2} and T_{PW} are 100% production tested. All other timing is verified by functional testing.

AC ELECTRICAL CHARACTERISTICS (CONTINUED)

AC Electrical Characteristics: Unless otherwise indicated, all parameters apply at $T_A = +25^{\circ}C$, $V_{DD} = 9V$, OSCAP = .1 μ F, RBIAS = 8.2 M Ω , $V_{SS} = 0V$.

$OSCAP = .1 \ \mu\text{F}, \text{RBIAS} = 8.2 \ \text{M}\Omega, \ \text{V}_{\text{SS}} = 0\text{V}.$									
Parameter		Symbol	Test Pin	Min	Тур	Max	Units	Conditions	
Horn On Tim	ie	T _{HON1}	10,11	450	500	550	ms	Operating, alarm condition, Note 1 , TONE = High	
		T _{HON2}	10,11	9.4	10.5	12.9	ms	Low battery, no alarm or PTT in alarm memory	
		T _{HON3}	10,11	150	167	183	ms	Operating, alarm condition, Note 1 , TONE = Low	
Horn Off Tim	ie	T _{HOF1}	10,11	450	500	550	ms	Operating, alarm condition, Note 1 , TONE = High	
			10,11	1.35	1.5	1.65	S	Operating, alarm condition, Note 1 , TONE = High	
		T _{HOF3}	10,11	75	83	92	ms	Operating, alarm condition, Note 1 , TONE = Low	
		T _{HOF4}	10,11	32	40	48	s	Low battery, no alarm	
		T _{HOF5}	10,11	216	240	264	ms	PTT in alarm memory	
I/O Charge Dump Duration		T _{IODMP}	2	1.34	1.67	2.0	S	At conclusion of local alarm or test	
I/O Delay		T _{IODLY1}	2	—	3	—	S	From start of local alarm to I/O active	
I/O Filter		T _{IOFILT}	2	_	—	450	ms	I/O as input, no local alarm	
Remote Alarm Delay		T _{IODLY2}	2	.450		2.75	S	No local alarm, I/O as input, from I/O active to horn active	
Timer	RE46C162	т	4	6	8	10	Min	No alarm	
Period	RE46C163	T _{TPER}	4	40	50	60	S	No alarm	
Alarm Memo Visual Indica		T _{AMTPER}	5	19.2	24	28.8	Hour	No alarm, alarm memory	

Note 1: See timing diagram for horn temporal and non-temporal patterns.

2: T_{PER1}, T_{PER2} and T_{PW} are 100% production tested. All other timing is verified by functional testing.

TEMPERATURE CHARACTERISTICS

Electrical Specifications: Unless otherwise indicated,							
Parameters	Sym	Min	Тур	Max	Units	Conditions	
Temperature Ranges							
Operating Temperature Range	Τ _Α	-10	_	+60	°C		
Storage Temperature Range	T _{STG}	-55	—	+125	°C		
Thermal Package Resistances							
Thermal Resistance, 16L-PDIP	θJ _A	—	70		°C/W		

2.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 2-1. TABLE 2-1: PIN FUNCTION TABLE

RE46C162/163	Nama	Description					
PDIP, SOIC	Name	Description					
1	TSTART	This input is used to invoke the push-to-test alarm, alarm memory indication, and the timer mode. This input has an internal pull-down.					
2	I/O	This bidirectional pin provides the capability to interconnect many detectors in a single system. This pin has an internal pull-down.					
3	TONE	This pin selects the NFPA72 horn tone (high) or the 2/3 duty cycle continuous tone (low).					
4	TSTROBE	This pin is strobed on with the internal clock in timer mode. A resistor connected to this pin is used to modify the detector sensitivity for the timer period.					
5	LED	Open drain NMOS output used to drive a visible LED.					
6	V _{DD}	Connect to the positive supply voltage.					
7	RBIAS	A resistor connected between this pin and V _{DD} sets the internal bias current.					
8	FEED	Usually connected to the feedback electrode through a current limiting resistor. If not used, this pin must be connected to V_{DD} or V_{SS} .					
9	V _{SS}	Connect to the negative supply voltage.					
10	HB	This pin is connected to the metal electrode of a piezoelectric transducer.					
11	HS	HS is a complementary output to HB and connects to the ceramic electrode of the piezoelectric transducer.					
12	OSCAP	A capacitor connected between this pin and V_{SS} sets the oscillator timing.					
13	VSEN	This pin can be used to modify the set point for the smoke comparator by use of external resistors to V_{DD} or $V_{SS}.$					
14	GUARD1	Output of the guard amplifier.					
15	DETECT	Connect to the collector electrode (CEV) of the ion smoke chamber.					
16	GUARD2	Output of the guard amplifier.					

3.0 DEVICE DESCRIPTION

3.1 Internal Timing

With external components as indicated on the application drawing, the period of the oscillator is nominally 1.67 seconds in standby. Every 1.67 seconds, the detection circuitry is powered up for 10.5 ms and the status of the smoke comparator is latched. In addition, every 40 seconds the LED driver is turned on for 10.5 ms and the status of the low battery comparator is latched. The smoke comparator status is not checked during the low battery test, during the low battery horn warning chirp, or when the horn is on due to an alarm condition.

If an alarm condition is detected, the oscillator period increases to 41.7 ms.

Due to the low current used in the oscillator, the capacitor on the OSCAP pin should be a low leakage type.

3.2 Smoke Detection Circuit

The smoke comparator compares the ionization chamber voltage to a voltage derived from a resistor divider across V_{DD} . This divider voltage is available externally on the VSEN pin. When smoke is detected, this voltage is internally increased by 130 mV nominal to provide hysteresis and make the detector less sensitive to false triggering.

The VSEN pin can be used to modify the internal set point for the smoke comparator by use of external resistors to V_{DD} or V_{SS} . Nominal values for the internal resistor divider are indicated on the block diagram. These internal resistor values can vary by up to ±20%, but the resistor matching should be <2% on any one device. The transmission switch on VSEN prevents any interaction from the external adjustment resistors.

The guard amplifier and outputs are always active and will be within 50 mV of the DETECT input to reduce surface leakage. The guard outputs also allow for measurement of the DETECT input without loading the ionization chamber.

3.3 Low Battery Detection

An internal reference is compared to the voltagedivided V_{DD} supply. The battery can be checked under load via the LED low side driver output since low battery status is latched at the end of the 10.5 ms LED pulse.

3.4 LED Pulse

The LED is pulsed on for 10.5 ms every 40s in standby. In alarm, the LED is pulsed on for 10.5 ms every 1 second.

3.5 Interconnect

The I/O pin provides a capability common to many detectors in a single system. If a single unit goes into alarm, the I/O pin is driven high. This high signal causes the interconnected units to alarm. The LED flashes every 1s for 10.5 ms on the signaling unit and is inhibited on the units that are in alarm due to the I/O signal. An internal sink device on the I/O pin helps to discharge the interconnect line. This charge dump device is active for 1 clock cycle after the unit exits the alarm condition (1.67s).

The interconnect input has a 500 ms nominal digital filter. This allows for interconnection to other types of alarms (carbon monoxide for example) that may have a pulsed interconnect signal.

3.6 Testing

At power-up all internal registers are reset. The low battery set point can be tested at power-up by holding FEED and OSCAP low at power-up. HB will change state as V_{DD} passes through the low battery set point. By holding the OSCAP pin low, the internal power strobe is active. Functional testing can be accelerated by driving OSCAP with a 4 kHz square wave; however, the 10.5 ms strobe period must be maintained for proper operation of the analog circuitry. Refer to Figure 3-1 timing diagram.

3.7 Timer Mode

The transition of the TSTART pin from a high to low level initiates a timer period (10 minutes maximum for RE46C162, and 1 minute maximum for RE46C163). During this timer period, the open drain NMOS on the TSTROBE pin is strobed simultaneously with the internal clock. A resistor connected to this pin and the VSEN pin is used to modify the detector sensitivity for the timer period.

During the timer period, the LED flashes for 10.5 ms every 10 seconds.

If the smoke level exceeds the reduced sensitivity set point during the timer period, the unit will go into a local alarm condition, the horn will sound and the timer mode is cancelled. If an external only alarm occurs during the timer mode, the timer mode is cancelled.

If the test button is pushed in a standby, reduced sensitivity mode, the unit is tested normally. Upon release of the test button, the timer mode counter is reset and restarted.

3.8 Alarm Memory

If a detector has entered a local alarm, once it exits the local alarm, the alarm memory latch is set. Initially the LED can be used to visually identify any unit that had previously been in a local alarm condition. The LED will flash 3 times spaced 3.3 seconds apart. This pattern will repeat every 40 seconds. The duration of the flash is 10.5 ms. In order to conserve battery power, this visual indication will stop after a period of 24 hours. The user will still be able to identify a unit with an active alarm memory by pressing the push-to-test button. When the push-to-test button is active, the horn will chirp for 10.5 ms every 250 ms.

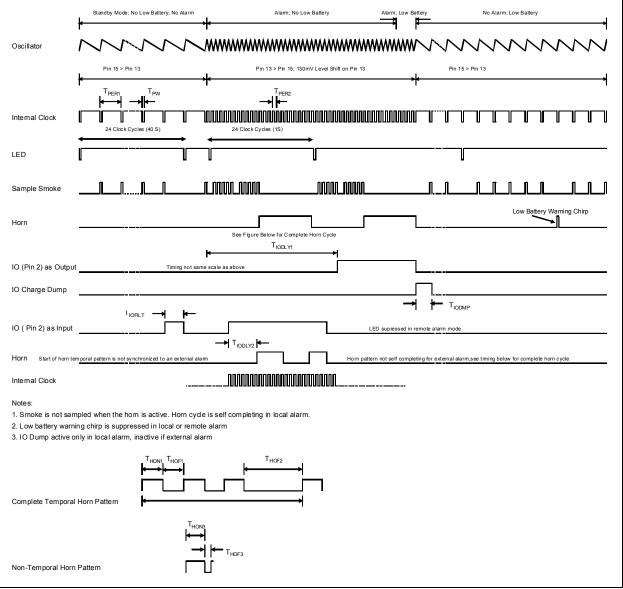
If the alarm memory condition is set, any time the pushto-test button is pressed and then released, the alarm memory latch is reset. The initial 24 hour visual indication is not displayed if a low battery condition exits.

3.9 Tone Select

The TONE pin selects the NFPA72 temporal horn tone (high), or the 2/3 duty cycle continuous tone (low). If this pin is externally connected high, use a current limiting resistor of at least 1.5K from TONE pin to V_{DD} .

3.10 Reverse Battery Protection

The RE46C162/163 internally limits the current from V_{SS} to V_{DD} in the event of accidental polarity reversal. If an input is connected to V_{DD} it should be done through a resistance of at least 1.5K to limit the reverse current through this path.





Timing Diagram – Standby, Local Alarm, Low Battery.

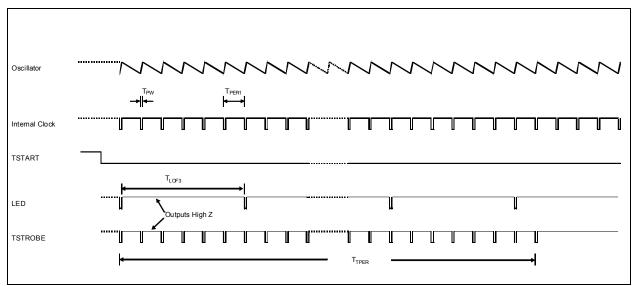
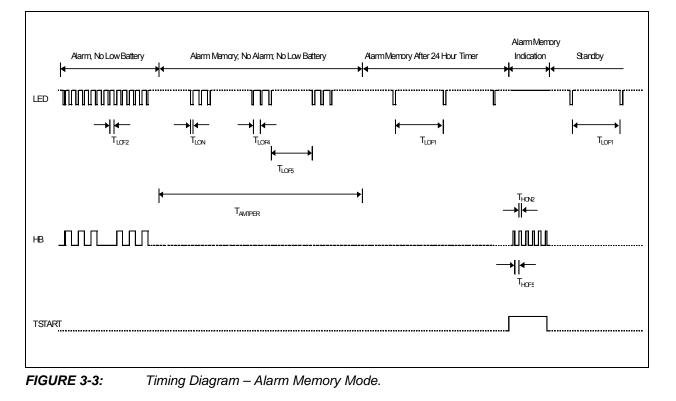


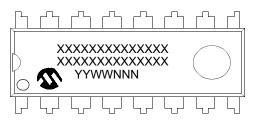
FIGURE 3-2: Timing Diagram – Timer Mode.

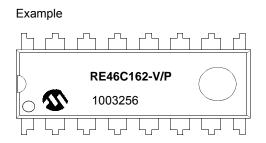


4.0 PACKAGING INFORMATION

4.1 Package Marking Information

16-Lead PDIP

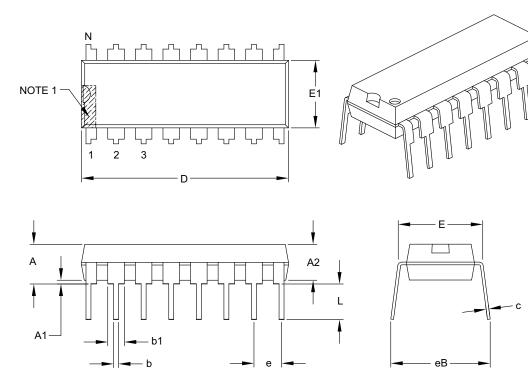




Legend:	XXX Y YY WW NNN (@3) *	Customer-specific information Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC designator for Matte Tin (Sn) This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.					
	In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.						

16-Lead Plastic Dual In-Line (P) – 300 mil Body [PDIP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	INCHES				
Di	mension Limits	MIN	NOM	MAX		
Number of Pins	N		16			
Pitch	е		.100 BSC			
Top to Seating Plane	A	-	-	.210		
Molded Package Thickness	A2	.115	.130	.195		
Base to Seating Plane	A1	.015	-	_		
Shoulder to Shoulder Width	E	.290	.310	.325		
Molded Package Width	E1	.240	.250	.280		
Overall Length	D	.735	.755	.775		
Tip to Seating Plane	L	.115	.130	.150		
Lead Thickness	С	.008	.010	.015		
Upper Lead Width	b1	.045	.060	.070		
Lower Lead Width	b	.014	.018	.022		
Overall Row Spacing §	eB	-	-	.430		

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

- 2. § Significant Characteristic.
- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-017B

APPENDIX A: REVISION HISTORY

Revision A (March 2010)

• Original Release of this Document.

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

ļ	PART NO. /	x xx	Examples:					
	Device Pac	kage Number of Pins	a) b)	RE46C162E16F: RE46C163E16F:	16LD PDIP Package. 16LD PDIP Package.			
	Device	RE46C162: CMOS Ionization Smoke Detector RE46C163: CMOS Ionization Smoke Detector						
	Package	E = Plastic Dual In-Line, 300 mil. Body, 16-Lead (PDIP)						

Note the following details of the code protection feature on Microchip devices:

- · Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

Code protection is constantly evolving. We at Microchip are committed to continuously improving the code protection features of our products. Attempts to break Microchip's code protection feature may be a violation of the Digital Millennium Copyright Act. If such acts allow unauthorized access to your software or other copyrighted work, you may have a right to sue for relief under that Act.

Information contained in this publication regarding device applications and the like is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. MICROCHIP MAKES NO REPRESENTATIONS OR WARRANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION, INCLUDING BUT NOT LIMITED TO ITS CONDITION, QUALITY, PERFORMANCE, MERCHANTABILITY OR FITNESS FOR PURPOSE. Microchip disclaims all liability arising from this information and its use. Use of Microchip devices in life support and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend, indemnify and hold harmless Microchip from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights.

QUALITY MANAGEMENT SYSTEM CERTIFIED BY DNV ISO/TS 16949:2002

Trademarks

The Microchip name and logo, the Microchip logo, dsPIC, KEELOQ, KEELOQ logo, MPLAB, PIC, PICmicro, PICSTART, PIC³² logo, rfPIC and UNI/O are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

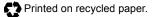
FilterLab, Hampshire, HI-TECH C, Linear Active Thermistor, MXDEV, MXLAB, SEEVAL and The Embedded Control Solutions Company are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Analog-for-the-Digital Age, Application Maestro, CodeGuard, dsPICDEM, dsPICDEM.net, dsPICworks, dsSPEAK, ECAN, ECONOMONITOR, FanSense, HI-TIDE, In-Circuit Serial Programming, ICSP, Mindi, MiWi, MPASM, MPLAB Certified logo, MPLIB, MPLINK, mTouch, Octopus, Omniscient Code Generation, PICC, PICC-18, PICDEM, PICDEM.net, PICkit, PICtail, REAL ICE, rfLAB, Select Mode, Total Endurance, TSHARC, UniWinDriver, WiperLock and ZENA are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

SQTP is a service mark of Microchip Technology Incorporated in the U.S.A.

All other trademarks mentioned herein are property of their respective companies.

© 2010, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.



ISBN: 978-1-60932-126-0

Microchip received ISO/TS-16949:2002 certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona; Gresham, Oregon and design centers in California and India. The Company's quality system processes and procedures are for its PIC® MCUs and dsPIC® DSCs, KEELoQ® code hopping devices, Serial EEPROMs, microperipherals, nonvolatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001:2000 certified.



WORLDWIDE SALES AND SERVICE

AMERICAS

Corporate Office 2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200 Fax: 480-792-7277 Technical Support: http://support.microchip.com Web Address: www.microchip.com

Atlanta Duluth, GA Tel: 678-957-9614 Fax: 678-957-1455

Boston Westborough, MA Tel: 774-760-0087 Fax: 774-760-0088

Chicago Itasca, IL Tel: 630-285-0071 Fax: 630-285-0075

Cleveland Independence, OH Tel: 216-447-0464 Fax: 216-447-0643

Dallas Addison, TX Tel: 972-818-7423 Fax: 972-818-2924

Detroit Farmington Hills, MI Tel: 248-538-2250 Fax: 248-538-2260

Kokomo Kokomo, IN Tel: 765-864-8360 Fax: 765-864-8387

Los Angeles Mission Viejo, CA Tel: 949-462-9523 Fax: 949-462-9608

Santa Clara Santa Clara, CA Tel: 408-961-6444 Fax: 408-961-6445

Toronto Mississauga, Ontario, Canada Tel: 905-673-0699 Fax: 905-673-6509

ASIA/PACIFIC

Asia Pacific Office Suites 3707-14, 37th Floor Tower 6, The Gateway Harbour City, Kowloon Hong Kong Tel: 852-2401-1200 Fax: 852-2401-3431 Australia - Sydney

Tel: 61-2-9868-6733 Fax: 61-2-9868-6755

China - Beijing Tel: 86-10-8528-2100 Fax: 86-10-8528-2104

China - Chengdu Tel: 86-28-8665-5511 Fax: 86-28-8665-7889

China - Chongqing Tel: 86-23-8980-9588 Fax: 86-23-8980-9500

China - Hong Kong SAR Tel: 852-2401-1200 Fax: 852-2401-3431

China - Nanjing Tel: 86-25-8473-2460

Fax: 86-25-8473-2470 China - Qingdao Tel: 86-532-8502-7355 Fax: 86-532-8502-7205

China - Shanghai Tel: 86-21-5407-5533 Fax: 86-21-5407-5066

China - Shenyang Tel: 86-24-2334-2829 Fax: 86-24-2334-2393

China - Shenzhen Tel: 86-755-8203-2660 Fax: 86-755-8203-1760

China - Wuhan Tel: 86-27-5980-5300 Fax: 86-27-5980-5118

China - Xian Tel: 86-29-8833-7252 Fax: 86-29-8833-7256

China - Xiamen Tel: 86-592-2388138 Fax: 86-592-2388130

China - Zhuhai Tel: 86-756-3210040 Fax: 86-756-3210049

ASIA/PACIFIC

India - Bangalore Tel: 91-80-3090-4444 Fax: 91-80-3090-4123

India - New Delhi Tel: 91-11-4160-8631 Fax: 91-11-4160-8632

India - Pune Tel: 91-20-2566-1512 Fax: 91-20-2566-1513

Japan - Yokohama Tel: 81-45-471- 6166 Fax: 81-45-471-6122

Korea - Daegu Tel: 82-53-744-4301 Fax: 82-53-744-4302

Korea - Seoul Tel: 82-2-554-7200 Fax: 82-2-558-5932 or 82-2-558-5934

Malaysia - Kuala Lumpur Tel: 60-3-6201-9857 Fax: 60-3-6201-9859

Malaysia - Penang Tel: 60-4-227-8870 Fax: 60-4-227-4068

Philippines - Manila Tel: 63-2-634-9065 Fax: 63-2-634-9069

Singapore Tel: 65-6334-8870 Fax: 65-6334-8850

Taiwan - Hsin Chu Tel: 886-3-6578-300 Fax: 886-3-6578-370

Taiwan - Kaohsiung Tel: 886-7-536-4818 Fax: 886-7-536-4803

Taiwan - Taipei Tel: 886-2-2500-6610 Fax: 886-2-2508-0102

Thailand - Bangkok Tel: 66-2-694-1351 Fax: 66-2-694-1350

EUROPE

Austria - Wels Tel: 43-7242-2244-39 Fax: 43-7242-2244-393 Denmark - Copenhagen Tel: 45-4450-2828 Fax: 45-4485-2829

France - Paris Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

Germany - Munich Tel: 49-89-627-144-0 Fax: 49-89-627-144-44

Italy - Milan Tel: 39-0331-742611 Fax: 39-0331-466781

Netherlands - Drunen Tel: 31-416-690399 Fax: 31-416-690340

Spain - Madrid Tel: 34-91-708-08-90 Fax: 34-91-708-08-91

UK - Wokingham Tel: 44-118-921-5869 Fax: 44-118-921-5820

01/05/10